



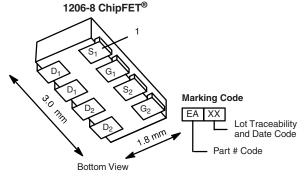
# Complementary 30 V (D-S) MOSFET

PRODUCT SUMMARY						
	V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
N-Channel	30	0.085 at V <sub>GS</sub> = 10 V	± 3.9			
		0.143 at V <sub>GS</sub> = 4.5 V	± 3.0			
P-Channel	- 30	0.165 at V <sub>GS</sub> = - 10 V	± 2.8			
		0.290 at V <sub>GS</sub> = - 4.5 V	± 2.1			

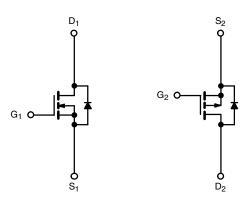
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si5504DC-T1-E3 (Lead (Pb)-free) Si5504DC-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted								
			N-Channel		P-Channel			
Parameter		Symbol	5 s	Steady State	5 s	Steady State	Unit	
Drain-Source Voltage		$V_{DS}$	30		- 30		V	
Gate-Source Voltage		$V_{GS}$	± 20				]	
Continuous Drain Courant (T. 150°C)	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	± 3.9	± 2.9	± 2.8	± 2.1		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 85 °C		± 2.8	± 2.1	± 2.0	± 1.5		
Pulsed Drain Current		I <sub>DM</sub>	± 10				Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.8	0.9	- 1.8	- 0.9		
Mariana Barra Birainating	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.1	1.1	2.1	1.1	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 85 °C		1.1	0.6	1.1	0.6		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150				°C	
Soldering Recommendations (Peak Temperature) <sup>b, c</sup>			260					

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Marrian II. and the Amelian to	t ≤ 5 s	R <sub>thJA</sub>	50	60	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	thJA	90	110			
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	30	40			

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See reliability manual for profile. The ChipFET/PowerPAK is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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<b>SPECIFICATIONS</b> $T_J = 25  ^{\circ}\text{C}$ , unless otherwise noted									
Parameter	Symbol	Test Conditions		Min.	Тур.	Max.	Unit		
Static									
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	N-Ch	1.0			V		
		$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	P-Ch	- 1.0			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	N-Ch			± 100	nA		
			P-Ch			± 100			
	I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V		N-Ch		1			
Zero Gate Voltage Drain Current		V <sub>DS</sub> = - 24 V, V <sub>GS</sub> = 0 V	P-Ch N-Ch			- 1	μΑ		
Ç		DO 7 GO 7 0				5	·		
		V <sub>DS</sub> = - 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	P-Ch			- 5			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	N-Ch	10			Α		
	D(OII)	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	P-Ch	- 10					
	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 2.9 \text{ A}$	N-Ch		0.072	0.085			
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 2.1 A	P-Ch		0.137	0.165	Ω		
Drain-Gource On-State Hesistance		$V_{GS} = 4.5 \text{ V}, I_D = 2.2 \text{ A}$	N-Ch		0.120	0.143	32		
		$V_{GS} = -4.5 \text{ V}, I_D = -1.6 \text{ A}$	P-Ch		0.240	0.290			
Forward Transconductance <sup>a</sup>	9fs	$V_{DS} = 15 \text{ V}, I_D = 2.9 \text{ A}$	N-Ch		6		s		
Forward Transconductance		$V_{DS} = -15 \text{ V}, I_{D} = -2.1 \text{ A}$	P-Ch		3		J		
Diada Farusard Valtaga	V <sub>SD</sub>	$I_S = 0.9 \text{ A}, V_{GS} = 0 \text{ V}$	N-Ch		0.8	1.2	٧		
Diode Forward Voltage <sup>a</sup>		$I_S = -0.9 \text{ A}, V_{GS} = 0 \text{ V}$	P-Ch		- 0.8	- 1.2	V		
Dynamic <sup>b</sup>									
Total Gate Charge	Qg	N-Channel	N-Ch		5	7.5			
		$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.9 \text{ A}$	P-Ch		5.5	6.6	nC		
Gate-Source Charge	$Q_{gs}$	b3 - 7 d3 - 7 b	N-Ch		0.8				
	Q <sub>gd</sub>	P-Channel	P-Ch N-Ch		1.2 1.0				
Gate-Drain Charge		$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -2.1 \text{ A}$	P-Ch		0.9				
	t <sub>d(on)</sub>	N-Channel	N-Ch		7	11			
Turn-On Delay Time			P-Ch		8	12			
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_L = 15 \Omega$	N-Ch		12	18			
Rise Time		$I_D \cong 1 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 6 \Omega$	P-Ch		11	18			
Turn-Off Delay Time	t <sub>d(off)</sub>	P-Channel	N-Ch		12	18	ns		
		$V_{DD} = -15 \text{ V}, R_L = 15 \Omega$	P-Ch		14	21	- 115		
Fall Time		$I_D\cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_g$ = 6 $\Omega$	N-Ch		7	11			
	<u>'</u>	L 0.0 A dl/dt 100 A /:	P-Ch		8	12			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = 0.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$	N-Ch		40	80			
		I <sub>F</sub> = - 0.9 A, dI/dt = 100 A/μs	P-Ch		40	80			

#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

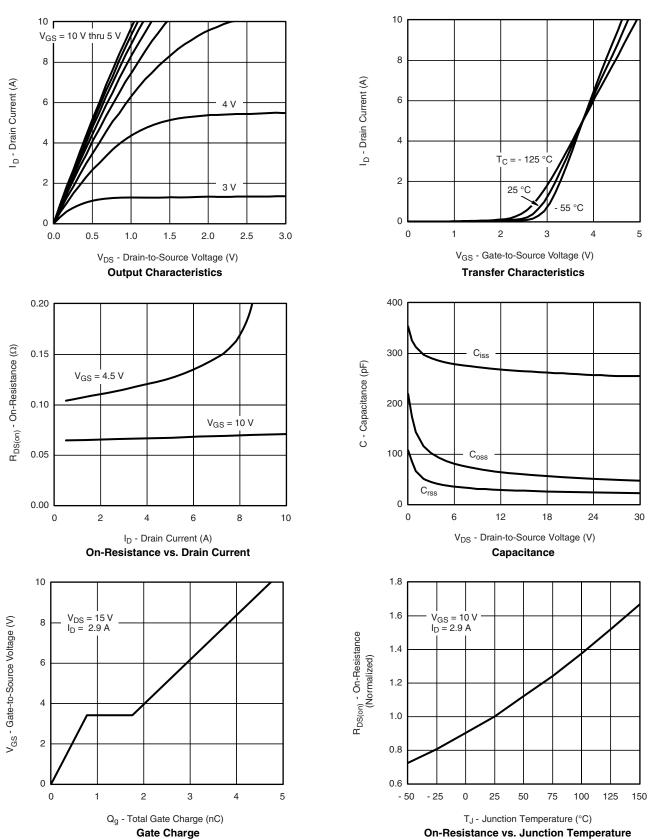
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.







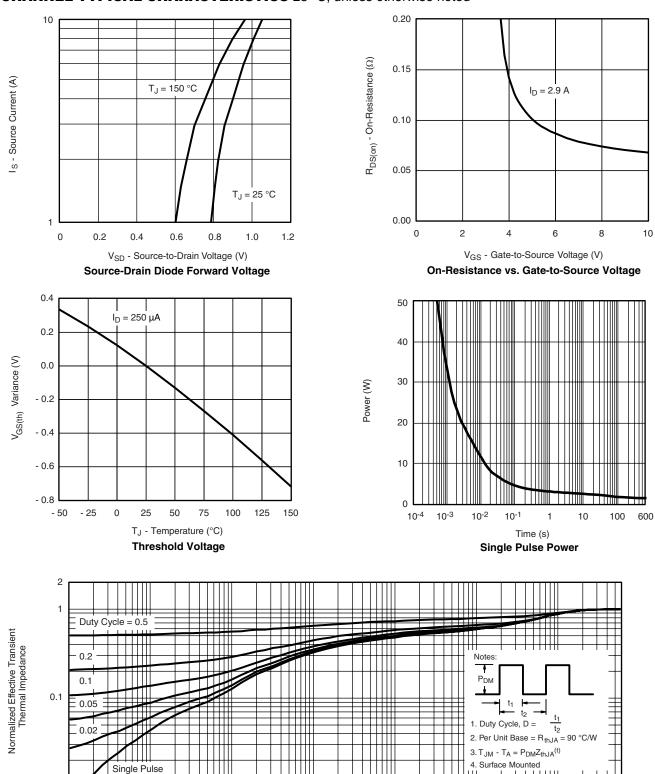
### N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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### N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



10-1

0.01

10-4

10-3

10-2

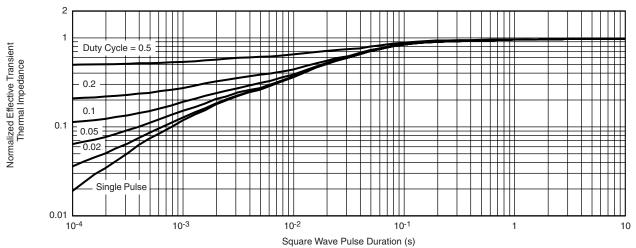
600

100

10

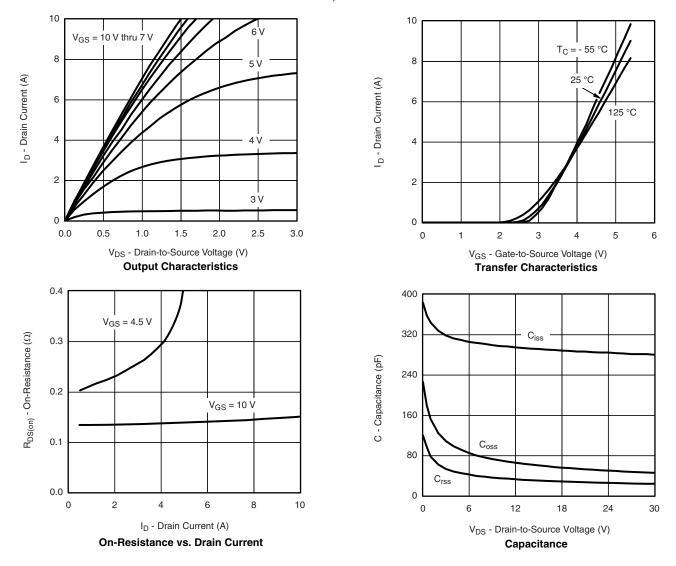


### N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

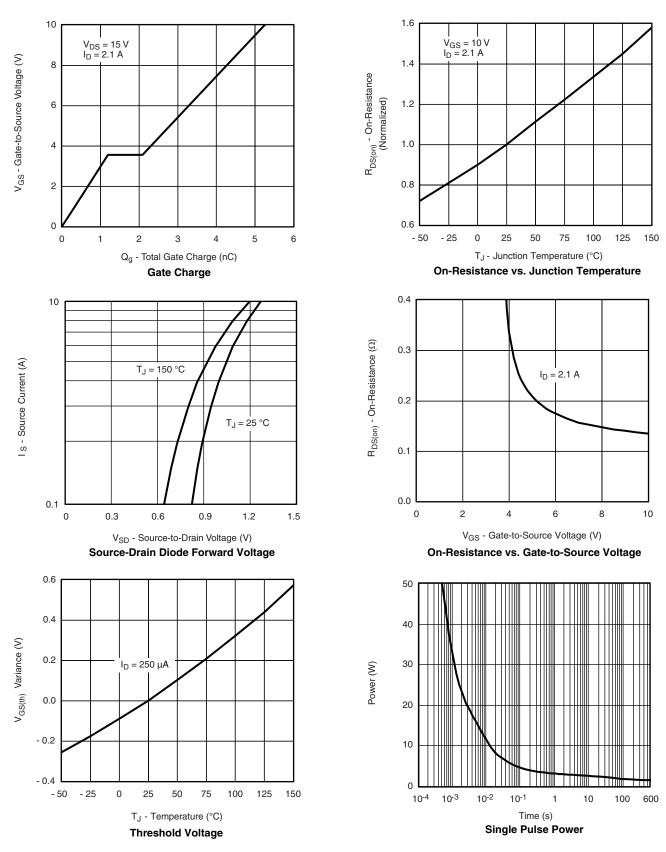
#### P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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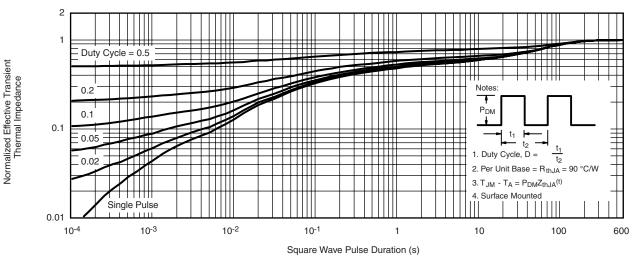


### P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

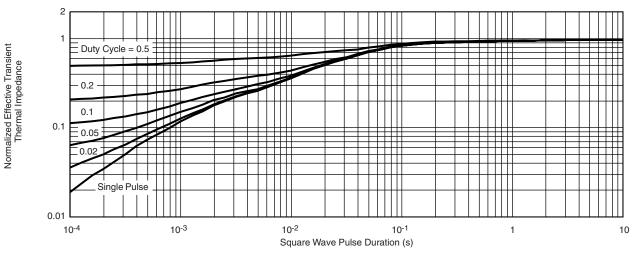




#### P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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